

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	15	"5747831".pn. "6617653".pn. "6380569".pn. "5396085".pn. "5945701".pn. "5753938".pn. "6767783".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/11 09:53
S2	70	(sic or silicon adj carbide or si adj c) near8 (sit or static near induction near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/11 13:07
S3	451	(sic or silicon adj carbide or si adj c) and (vertical or trench) near2 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/11 13:08
S4	283	(sic or silicon adj carbide or si adj c) and (vertical or trench) near channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/11 13:08
S5	240	(sic or silicon adj carbide or si adj c) and (vertical or trench) near2 channel and (fet or mosfet or nmos or pmos or cmos or misfet or mesfet or field near2 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/11 15:28
S6	121	(sic or silicon adj carbide or si adj c) and (trench or trenched or groove or grooved) near gate and drift	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/11 16:48
S7	35	(sic or silicon adj carbide or si adj c) and (trench or trenched or groove or grooved) near3 (doping or doped or implant or implanted or implanting or dopant or impurity) near3 (control or channel or controlling)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/11 16:49